

## **Amendments to the Claims**

This listing of claims will replace all prior versions, and listings, of claims in the application:

### **Listing of Claims:**

1. (Currently Amended) Support system for an apparatus of the type suitable to treat substrates and/or wafers, comprising:
  - a fixed base element having a substantially flat surface in which a substantially cylindrical seat with a substantially flat bottom is formed, and
  - the support element according to claim 22, the support element being housed inside the seat and being able to rotate about the axis of the seat;wherein the support system ~~element~~ comprises one or more passages for one or more of the gas flows, in which said passages emerge inside the seat in directions which are inclined and preferably skew with respect to said axis, in such a way as to lift and rotate the support element.
2. (Original) System according to Claim 1, wherein the support element is designed to remain substantially inside the seat, preferably with its upper side substantially aligned with the surface of the base element both when it is stationary and when it is in movement.
3. (Previously Presented) System according to Claim 1, wherein an annular channel for collecting the gas emitted from the passages, is formed in the seat.
4. (Currently Amended) System according to Claim 1, wherein the passages are branches of a ~~[[the]]~~ same pipe ~~(14)~~.
5. (Previously Presented) System according to Claim 1, wherein the passages are only two and are arranged in symmetrical positions with respect to said axis.
6. (Previously Presented) System according to Claim 1, wherein a pin and a corresponding hole are provided for guiding the rotation of the support element.

7. (Currently Amended) System according to Claim 6, wherein a cylindrical protuberance with a cylindrical hole is provided in the centre of the seat of the base element (10), in which a cylindrical recess with a cylindrical pin is provided in the centre of the bottom side of the support element and in which the pin of the support element is inserted in the hole of the base element and the protuberance of the base element is inserted in the recess of the support element.
8. (Previously Presented) System according to Claim 1, wherein the depressed areas are shaped so that the gas flows emerging from the passages exert the thrust thereon, said areas being preferably all identical and arranged symmetrically with respect to said axis.
9. (Original) System according to Claim 8, wherein said areas are bounded by three or four sides.
10. (Original) System according to Claim 9, wherein said areas have at least one straight side.
11. (Previously Presented) System according to Claim 9, wherein said areas have at least one curved side.
12. (Previously Presented) System according to Claim 9, wherein said areas have a variable depth.
13. (Original) System according to Claim 12, wherein the depth of said areas diminishes or increases in the radial direction with respect to the axis of rotation.
14. (Previously Presented) System according to Claim 12, wherein the depth of said areas diminishes or increases in the tangential direction with respect to the axis of rotation.
15. (Previously Presented) System according to Claim 8, wherein said areas reach the edge of the bottom side of the support element.

16. (Previously Presented) System according to Claim 15, wherein one side of said areas coincides with a section of an edge of the bottom side of the support element.
17. (Previously Presented) System according to Claim 8, wherein said areas have an edge, said edge being positioned and shaped in such a way that the gas flows emerging from the passages exert a thrust on said edge.
18. (Previously Presented) System according to Claim 1, wherein the support element is able to act also as a susceptor.
19. (Previously Presented) System according to Claim 1, characterized in that it is suitable for loading/unloading of the support element into/from the base element.
20. (Previously Presented) Reactor for epitaxial growth of semiconductor materials on substrates, wherein it comprises a support system for substrates according to Claim 1.
21. (Previously Presented) Apparatus for high-temperature thermal treatment of wafers, wherein it comprises a support system for wafers according to Claim 1.
22. (Previously Presented) Support element for an apparatus of the type designed to treat substrates and/wafers, having a substantially disc-shaped form with a substantially flat upper side provided with at least one cavity for a substrate or wafer and with a substantially flat bottom side, wherein the bottom side is provided with depressed areas shaped to receive the thrust of gas flows.
23. (Original) Element according to Claim 22, wherein said areas are bounded by three or four sides.
24. (Original) Element according to Claim 23, wherein said areas have at least one straight side.

25. (Previously Presented) Element according to Claim 22, wherein said areas have at least one curved side.
26. (Previously Presented) Element according to Claim 22 or, wherein said areas have a variable depth.
27. (Currently Amended) Element according to Claim 26, wherein the depth of said areas ~~(22)~~ diminishes or increases in the radial direction with respect to its axis.
28. (Currently Amended) Element according to Claim 26, wherein the depth of said areas ~~(22)~~ diminishes or increases in the tangential direction with respect to its axis.
29. (Previously Presented) Element according to Claim 22, wherein said areas reach the edge of its bottom side.
30. (Original) Element according to Claim 29, wherein one side of said areas coincides with a section of the edge of its bottom side.
31. (Previously Presented) Element according to Claim 22, wherein said areas have an edge, said edge being positioned and shaped to receive the thrust of gas flows.
32. (Previously Presented) Element according to Claim 22, characterized in that it is able to act also as a susceptor.